

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A method for fabricating a semiconductor film comprising:

irradiating a semiconductor film formed over a substrate with a laser beam to crystallize the semiconductor film,

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

2. (Original) A method for fabricating a semiconductor film according to claim 1, wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

3. (Previously Presented) A method for fabricating a semiconductor film comprising:

holding a substrate over a stage having pores wherein the substrate is provided with a semiconductor film; and

spouting gases from the pores to the substrate; and

irradiating the semiconductor film formed over the substrate with a laser beam,

wherein during irradiating the laser beam, ultrasonic vibration is applied to the substrate through a chuck, and

wherein during irradiating the laser beam, the substrate is floated by the chuck holding an end portion of the substrate and by spouting gases from the pores to the substrate.

4. (Original) A method for fabricating a semiconductor film according to claim 3, wherein said laser beam is a YVO_4 , a YAG, a YLF or an excimer laser.

5. (Previously Presented) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate;
and

irradiating the semiconductor film with a laser beam,

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

6. (Original) A method for fabricating a semiconductor device according to claim 5,

wherein said laser beam is a YVO_4 , a YAG, a YLF or an excimer laser.

7. (Original) A method for fabricating a semiconductor device according to claim 5,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

8. (Previously Presented) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate;
and

irradiating the semiconductor film with a laser beam condensed into a linear shape in an oxygen atmosphere, and

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

9. (Original) A method for fabricating a semiconductor device according to claim 8,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

10. (Original) A method for fabricating a semiconductor device according to claim 8,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

11. (Previously Presented) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate;

irradiating the semiconductor film with a laser beam condensed into a linear shape; and

crystallizing a whole surface of the semiconductor film while overlapping a beam spot of the laser beam on the semiconductor film,

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

12. (Original) A method for fabricating a semiconductor device according to claim 11,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

13. (Original) A method for fabricating a semiconductor device according to claim 11,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

14. (Previously Presented) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate;

crystallizing the semiconductor film having an amorphous structure by adding a metal element or a metal compound having catalytic action for enhancing a crystallization of the semiconductor film and by heat-treating; and

irradiating the semiconductor film with a laser beam condensed into a linear shape,

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

15. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said laser beam is a YVO_4 , a YAG, a YLF or an excimer laser.

16. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

17. (Original) A method for fabricating a semiconductor device according to claim 14,

wherein said metal element is nickel or platinum.

18. (Previously Presented) A method for fabricating a semiconductor device comprising:

forming a semiconductor film having an amorphous structure over a substrate;

crystallizing the semiconductor film having the amorphous structure by adding a metal element or a metal compound having catalytic action for enhancing a crystallization of the semiconductor film and by heat-treating;

irradiating the semiconductor film with a laser beam condensed into a linear beam; and

improving a crystallinity of the semiconductor film while overlapping a beam spot of the laser beam on the semiconductor film,

wherein ultrasonic vibration is applied to the substrate through a chuck during irradiating the laser beam, and

wherein the substrate is floated by the chuck holding an end portion of the substrate during irradiating the laser beam.

19. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said laser beam is a YVO₄, a YAG, a YLF or an excimer laser.

20. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said semiconductor device is used for a display device selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a sound reproduction device, a lap-top personal computer, a game machine, a portable information terminal, and an image reproduction device.

21. (Original) A method for fabricating a semiconductor device according to claim 18,

wherein said metal element is nickel or platinum.

22.-25. (Canceled)

26. (New) A method for fabricating a semiconductor device according to claim 1,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

27. (New) A method for fabricating a semiconductor device according to claim 3,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

28. (New) A method for fabricating a semiconductor device according to claim 5,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

29. (New) A method for fabricating a semiconductor device according to claim 8,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

30. (New) A method for fabricating a semiconductor device according to claim 11,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

31. (New) A method for fabricating a semiconductor device according to claim 14,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.

32. (New) A method for fabricating a semiconductor device according to claim 18,

wherein a gas is supplied to a surface of the semiconductor film irradiated with the laser beam during irradiating the laser beam.